

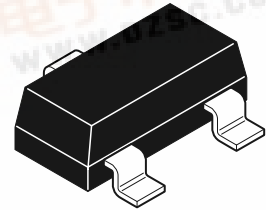


# ZXTN25020BFH

## 20V, SOT23, NPN medium power transistor

### Summary

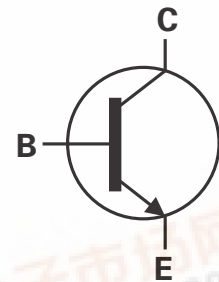
- $BV_{CEX} > 50V$
- $BV_{CEO} > 20V$
- $BV_{ECO} > 3V$
- $I_{C(cont)} = 4.5A$
- $V_{CE(sat)} < 45\text{ mV @ } 1A$
- $R_{CE(sat)} = 27\text{ m}\Omega$
- $P_D = 1.25W$



Complementary part number ZXTP25020BFH

### Description

Advanced process capability and package design have been used to maximize the power handling and performance of this small outline transistor. The compact size and ratings of this device make it ideally suited to applications where space is at a premium.

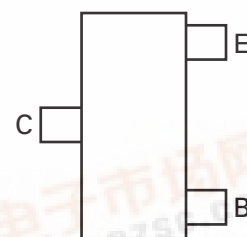


### Features

- High power dissipation SOT23 package
- High peak current
- Low saturation voltage
- 50V forward blocking voltage
- 3V reverse blocking voltage

### Applications

- MOSFET gate drivers
- Motor control
- DC-DC converters



Pinout - top view

### Ordering information

Device	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTN25020BFHTA	7	8	3,000

### Device marking

1B1

# ZXTN25020BFH

## Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Collector-base voltage	$V_{CBO}$	50	V
Collector-emitter voltage (forward blocking)	$V_{CEX}$	50	V
Collector-emitter voltage	$V_{CEO}$	20	V
Emitter-collector voltage (reverse blocking)	$V_{ECO}$	3	V
Emitter-base voltage	$V_{EBO}$	7	V
Continuous collector current <sup>(c)</sup>	$I_C$	4.5	A
Base current	$I_B$	1	A
Peak pulse current	$I_{CM}$	10	A
Power dissipation at $T_{amb} = 25^{\circ}C^{(a)}$	$P_D$	0.73	W
Linear derating factor		5.84	mW/°C
Power dissipation at $T_{amb} = 25^{\circ}C^{(b)}$	$P_D$	1.05	W
Linear derating factor		8.4	mW/°C
Power dissipation at $T_{amb} = 25^{\circ}C^{(c)}$	$P_D$	1.25	W
Linear derating factor		9.6	mW/°C
Power dissipation at $T_{amb} = 25^{\circ}C^{(d)}$	$P_D$	1.81	W
Linear derating factor		14.5	mW/°C
Operating and storage temperature range	$T_j, T_{stg}$	- 55 to 150	°C

## Thermal graphs

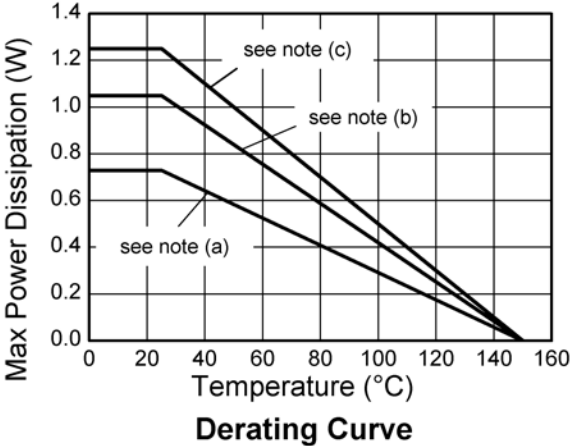
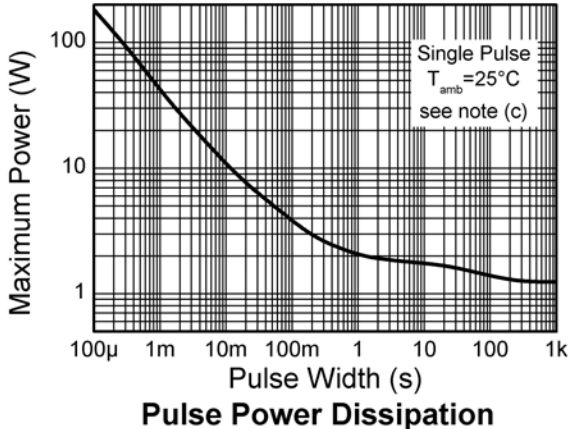
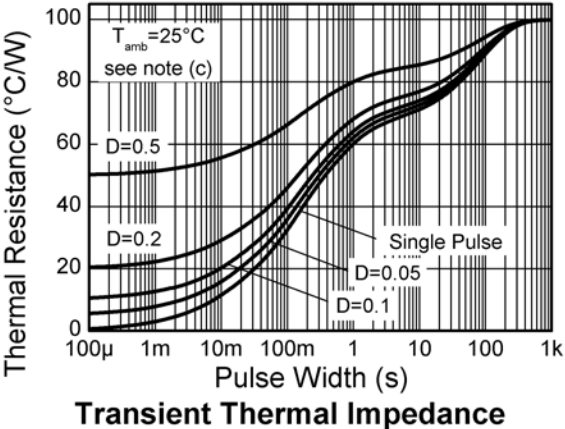
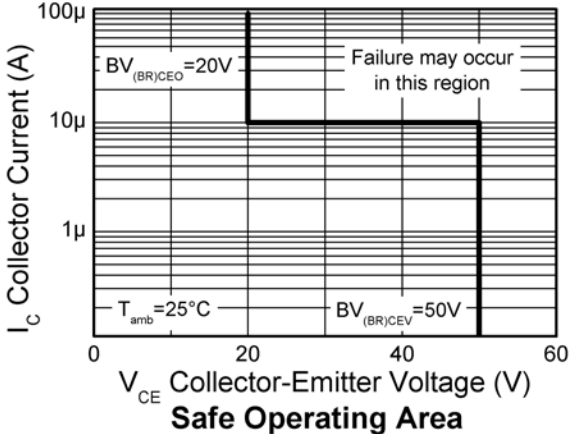
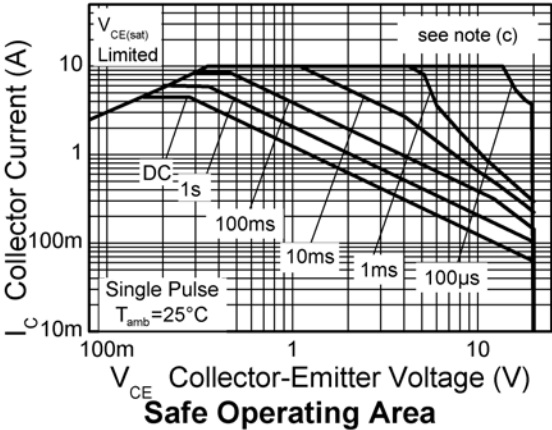
Parameter	Symbol	Limit	Unit
Junction to ambient <sup>(a)</sup>	$R_{\theta JA}$	171	°C/W
Junction to ambient <sup>(b)</sup>	$R_{\theta JA}$	119	°C/W
Junction to ambient <sup>(c)</sup>	$R_{\theta JA}$	100	°C/W
Junction to ambient <sup>(d)</sup>	$R_{\theta JA}$	69	°C/W

### NOTES:

- (a) For a device surface mounted on 15mm x 15mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.
- (b) Mounted on 25mm x 25mm x 1.6mm FR4 PCB with a high coverage of single sided 2 oz copper in still air conditions.
- (c) Mounted on 50mm x 50mm x 1.6mm FR4 PCB with a high coverage of single sided 2 oz copper in still air conditions.
- (d) As (c) above measured at  $t < 5$ secs.

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## Characteristics



# ZXTN25020BFH

## Electrical characteristics (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated)

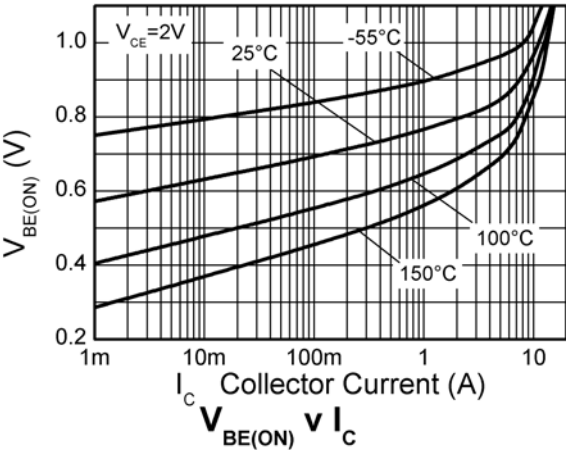
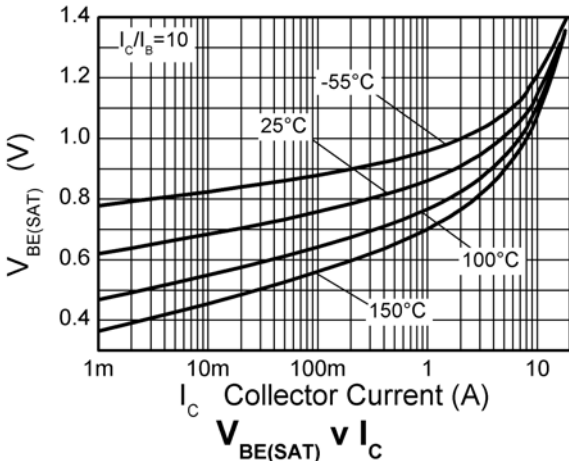
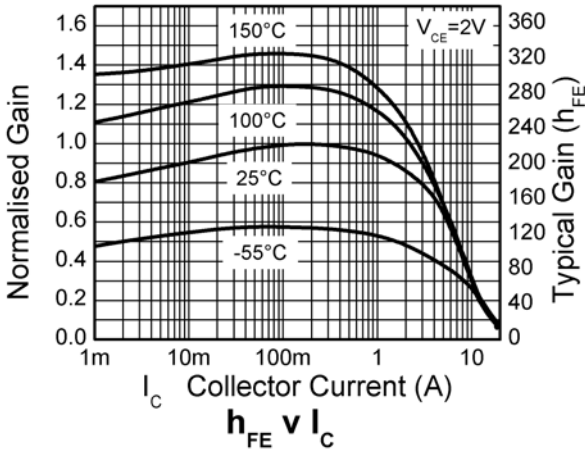
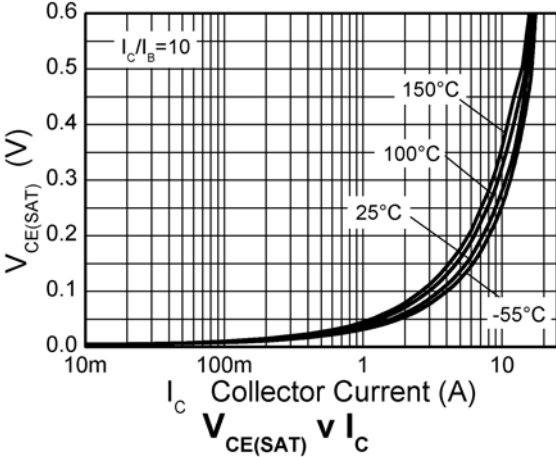
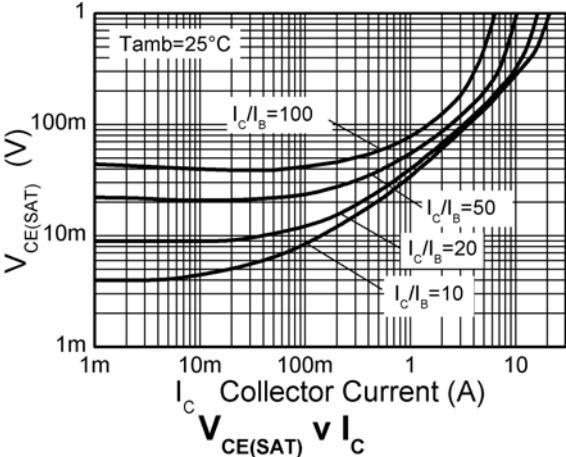
Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	$BV_{CBO}$	50	90		V	$I_C = 100\mu\text{A}$
Collector-emitter breakdown voltage (forward blocking)	$BV_{CEX}$	50	90			$I_C = 100\mu\text{A}$ , $R_{BE} < 1\text{k}\Omega$ or $-1\text{V} < V_{BE} < 0.25\text{V}$
Collector-emitter breakdown voltage (base open)	$BV_{CEO}$	20	27		V	$I_C = 10\text{mA}^{(*)}$
Emitter-base breakdown voltage	$BV_{EBO}$	7	8		V	$I_E = 100\mu\text{A}$
Emitter-collector breakdown voltage (reverse blocking)	$BV_{ECX}$	6	7		V	$I_E = 100\mu\text{A}$ , $R_{BC} < 1\text{k}\Omega$ or $0.25\text{V} > V_{BC} > -0.25\text{V}$
Emitter-collector breakdown voltage (base open)	$BV_{ECO}$	3	4.7		V	$I_E = 100\mu\text{A}$ ,
Collector-base cut-off current	$I_{CBO}$		<1	50 20	nA $\mu\text{A}$	$V_{CB} = 40\text{V}$ $V_{CB} = 40\text{V}$ , $T_{amb} = 100^{\circ}\text{C}$
Collector-emitter cut-off current	$I_{CEX}$		-	100	nA	$V_{CE} = 40\text{V}$ ; $R_{BE} < 1\text{k}\Omega$ or $-1\text{V} < V_{BE} < 0.25\text{V}$
Emitter-base cut-off current	$I_{EBO}$		<1	50	nA	$V_{EB} = 5.6\text{V}$
Collector-emitter saturation voltage	$V_{CE(sat)}$		35	45	mV	$I_C = 1\text{A}$ , $I_B = 100\text{mA}^{(*)}$
			55	80	mV	$I_C = 1\text{A}$ , $I_B = 20\text{mA}^{(*)}$
			90	115	mV	$I_C = 2\text{A}$ , $I_B = 40\text{mA}^{(*)}$
			175	240	mV	$I_C = 4.5\text{A}$ , $I_B = 90\text{mA}^{(*)}$
			120	145	mV	$I_C = 4.5\text{A}$ , $I_B = 450\text{mA}^{(*)}$
Base-emitter saturation voltage	$V_{BE(sat)}$		910	1000	mV	$I_C = 4.5\text{A}$ , $I_B = 90\text{mA}^{(*)}$
Base-emitter turn-on voltage	$V_{BE(on)}$		825	900	mV	$I_C = 4.5\text{A}$ , $V_{CE} = 2\text{V}^{(*)}$
Static forward current transfer ratio	$h_{FE}$	100	200	300		$I_C = 10\text{mA}$ , $V_{CE} = 2\text{V}^{(*)}$
		100	210			$I_C = 1\text{A}$ , $V_{CE} = 2\text{V}^{(*)}$
		75	160			$I_C = 4.5\text{A}$ , $V_{CE} = 2\text{V}^{(*)}$
		30	70			$I_C = 10\text{A}$ , $V_{CE} = 2\text{V}^{(*)}$
Transition frequency	$f_T$		185		MHz	$I_C = 50\text{mA}$ , $V_{CE} = 10\text{V}$ $f = 100\text{MHz}$
Output capacitance	$C_{OBO}$		22.7	30	pF	$V_{CB} = 10\text{V}$ , $f = 1\text{MHz}^{(*)}$
Delay time	$t_d$		87		ns	$V_{CC} = 10\text{V}$ .
Rise time	$t_r$		119		ns	$I_C = 1\text{A}$ ,
Storage time	$t_s$		146		ns	$I_{B1} = I_{B2} = 10\text{mA}$ .
Fall time	$t_f$		61		ns	

### NOTES:

(\*) Measured under pulsed conditions. Pulse width  $\leq 300\mu\text{s}$ ; duty cycle  $\leq 2\%$ .

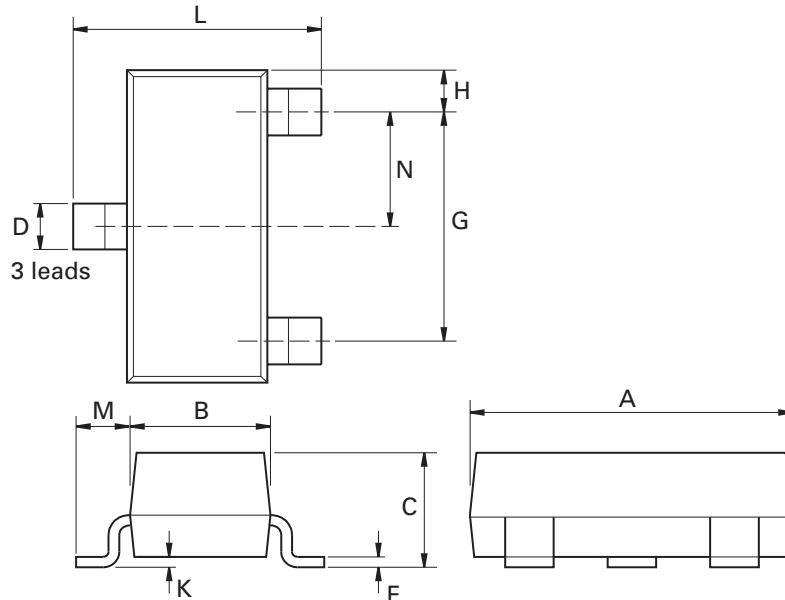
# ZXTN25020BFH

## Typical characteristics



# ZXTN25020BFH

## Package outline - SOT23



Dim.	Millimeters		Inches		Dim.	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Max.	Max.
A	2.67	3.05	0.105	0.120	H	0.33	0.51	0.013	0.020
B	1.20	1.40	0.047	0.055	K	0.01	0.10	0.0004	0.004
C	-	1.10	-	0.043	L	2.10	2.50	0.083	0.0985
D	0.37	0.53	0.015	0.021	M	0.45	0.64	0.018	0.025
F	0.085	0.15	0.0034	0.0059	N	0.95 NOM		0.0375 NOM	
G	1.90 NOM		0.075 NOM		-	-	-	-	-

**Note:** Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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